編號: 168

國立成功大學 108 學年度碩士班招生考試試題

系 所:電機工程學系 考試科目:電子材料概論

考試日期:0223,節次:2

第1頁,共2頁

※ 考生請注意:本試題不可使用計算機。 請於答案卷(卡)作答,於本試題紙上作答者,不予計分。

- 1. Briefly explain the following items (20%)
- (a) Screw dislocation
- (b) Bragg's law
- (c) Intermetallic compounds
- (d) Piezoelectric material
- (e) Seeback effect
- (f) Fick's first law
- (g) Grain boundary
- (h) Hall effect
- (i) Eutectic reaction
- (j) Ferromagnetism
- 2. Compare the atomic packing factors (the volume fraction of atoms in an unit cell) of the bcc, fcc, and hcp crystal structures. (10 %)
- 3. To form a solid solution, the Hume-Rothery rule is the main criterion. Based on this rule, please indicate which one of Zn (atomic radius=0.133) and Ni atomic radius=0.1246) is easier to form a solid solution with the Cu (atomic radius=0.125 nm). (10%)
- 4. Draw direction vectors in unit cell for the following directions. (10%)
 - (a) [110] (b) [210] (c) [112]
- 5. Compare the bonding types and electric conductivity of polymer, semiconductor and metal. (15%)
- 6. Calculate the planar atomic density in atoms per square millimeter for the (0001) plane in HCP beryllium, which has a lattice constant a=0.22856 nm and a c constant of 0.35832 nm. (10%)
- 7. Calculate the electrical resistivity of intrinsic silicon at 300 K. For Si at 300 K, the intrinsic carrier concentration $n_i=1.5*10^{16}$ carriers/m³, the electronic charge $q=1.60*10^{-19}$ C, electron mobility = 0.135 m²/V-s, and hole mobility=0.048 m²/V-s. (10%)

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第2頁,共2頁

- 8. If 500g of a 40 wt % Ag-60 wt % Cu alloy is slowly cooled from 1000°C to just below 780°C (15 %)
 - (a) How many grams of liquid and proeutectic alpha are present at 850 °C?
 - (b) How many grams of liquid and proeutectic alpha are present at temperature just above 780°C?
 - (c) How many grams of alpha are present in the eutectic structure at temperature just below 780°C?

